4Tb TLC NAND Flash

For space applications demanding the highest reliability for the most extreme environments, Frontgrade offers the industry's highest density, UT81NDQ512G8T, 4Tb TLC NAND Flash.



Frontgrade's NAND Flash is based on the Triple-Level Cell (TLC) NAND technology offering some of the highest density devices available in a single JEDEC 132-BGA package. This high-performance memory device is packaged in a JEDEC standard single 132-Plastic Ball Grid Array (PBGA). The device supports synchronous and asynchronous data interfaces to transfer commands, address, and data within each die and is Open NAND Flash Interface (ONFI) 4.0 compliant. The UT81NDQ512G8T follows the PEM-INST-001 (NASA EEE-INST-002) – Level 2 flow qualification.



UT81NDQ512G8T Block Diagram

4Tb TLC NAND Flash UT81NDQ512G8T

FEATURES:	 4Tb density +3.3V Core and +1.8V, +1.2V I/O Supply Voltage Open NAND Flash Interface (ONFI) 4.0 Compliant Triple-Level Cell (TLC) Technology Organization Page Size: x8 18,592 Bytes Block Size: 2304 Pages Plane Size: 4 planes x 504 blocks Device Size: 16,128 Blocks Synchronous I/O Performance NV-DDR2 Support (533MT/s r/w throughput per pin) NV-DDR3 Support (667MT/s r/w throughput per pin) NV-DDR3 Support (667MT/s r/w throughput per pin) Asynchronous I/O Performance tRC/tWC: 20 ns (min) Array Performance Read Page: 74 uS (typical) Erase Block: 15 ms (typical) Data Retention: JESD47G Compliant Complex Super (SI C mode) AU K Program/Erase Cycles (TLC mode) AU K Program/Erase Cycles (SI C mode)
APPLICATIONS:	 Solid-State Drives Solid-State Recorders Reconfigurable Computing Imaging and Communications Data Buffering Space Computing
OPERATIONAL ENVIRONMENT:	 Temp Range: -40°C to +85°C Total Ionizing Dose (TID): 50 krad(Si)* SEL Immune: ≤ 55 MeV-cm2/mg @ 85°C*
PHYSICAL:	JEDEC 132-PBGA, 1mm pitch
POWER:	 <300mW (typical per active die)
QUALIFICATIONS:	PEM-INST-001 (NASA EEE-INST-002) – Level 2*

* Product in development, targeted specification